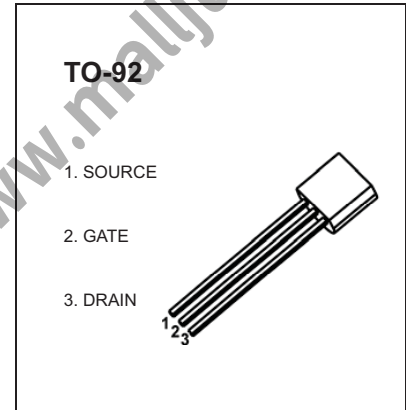


TO-92 Plastic-Encapsulate MOSFETS

2N7000

MOSFET (N-Channel)

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
60 V	5Ω@10V	200mA
	6Ω@4.5V	



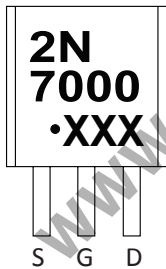
FEATURE

- High density cell design for low $R_{DS(ON)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability

APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

MARKING

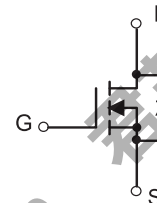


2N7000=Device code

Solid dot=Green molding compound device,
if none,the normal device

XXX=Code

Equivalent Circuit



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2N7000	TO-92	Bulk	1000pcs/Bag
2N7000-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Continuous Drain Current	I_D	0.2	A
Power Dissipation	P_D	0.625	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ +150	

MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25^{\circ}\text{C}$ unless otherwise specified

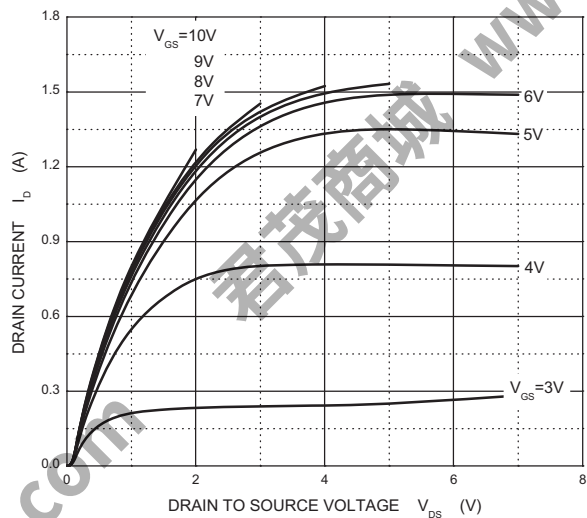
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}$, $I_D=10\mu\text{A}$	60			V
Gate-Threshold Voltage*	$V_{(GS)th}$	$V_{DS}=V_{GS}$, $I_D=1\text{mA}$	0.8		3	
Gate-body Leakage	I_{GSS}	$V_{DS}=0\text{ V}$, $V_{GS}=\pm 15\text{ V}$			± 10	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60\text{ V}$, $V_{GS}=0\text{ V}$			1	μA
On-state Drain Current	$I_{D(ON)}$	$V_{GS}=4.5\text{ V}$, $V_{DS}=10\text{ V}$	75			mA
Drain-Source On-Resistance*	$R_{DS(on)}$	$V_{GS}=4.5\text{V}$, $I_D=75\text{mA}$			6	Ω
		$V_{GS}=10\text{V}$, $I_D=500\text{mA}$			5	
Forward Trans conductance*	g_{fs}	$V_{DS}=10\text{ V}$, $I_D=200\text{mA}$	100			ms
Drain-source on-voltage*	$V_{DS(on)}$	$V_{GS}=10\text{V}$, $I_D=500\text{mA}$			2.5	V
		$V_{GS}=4.5\text{V}$, $I_D=75\text{mA}$			0.45	V
Input Capacitance **	C_{iss}	$V_{DS}=25\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$			60	pF
Output Capacitance **	C_{oss}				25	
Reverse Transfer Capacitance **	C_{rss}				5	
Turn-on Time **	$t_{d(on)}$	$V_{DD}=15\text{ V}$, $R_L=30\Omega$ $I_D=500\text{mA}$, $V_{GEN}=10\text{ V}$			10	ns
Turn-off Time **	$t_{d(off)}$	$R_G=25\Omega$			10	

*Pulse test

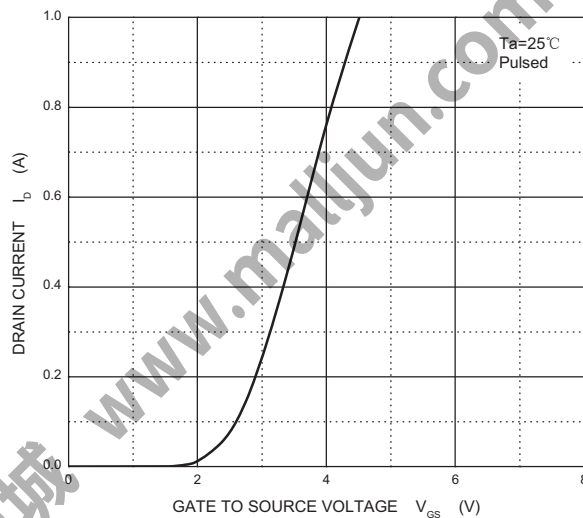
**These parameters have no way to verify.

Typical Characteristics

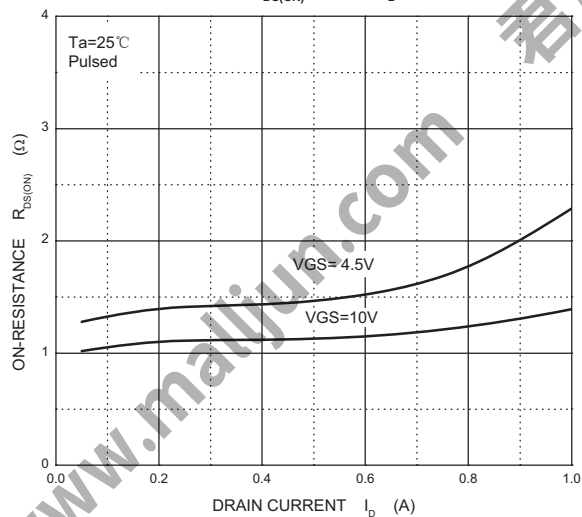
Output Characteristics



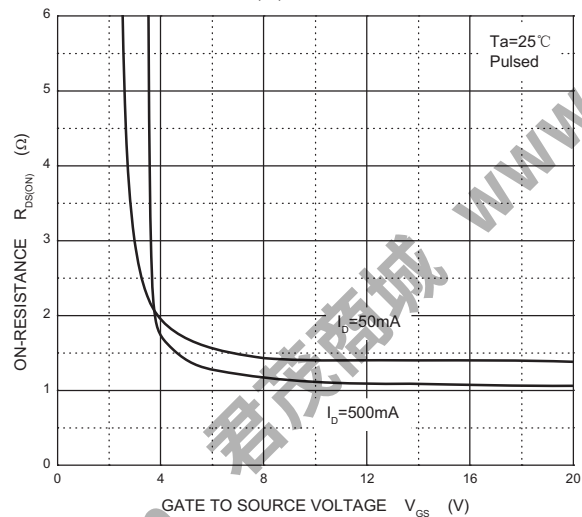
Transfer Characteristics



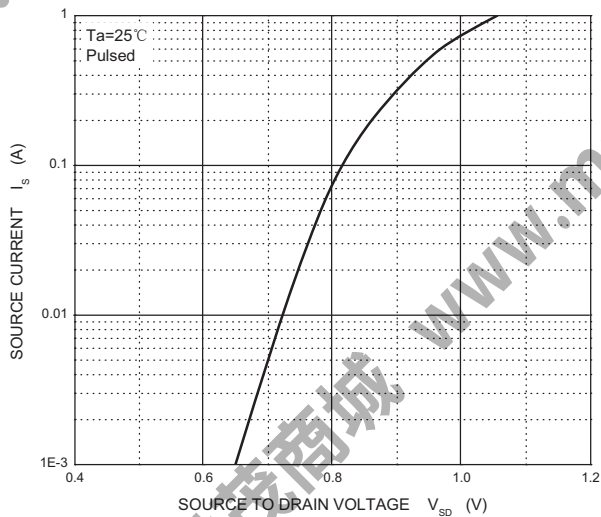
$R_{DS(ON)}$ — I_D



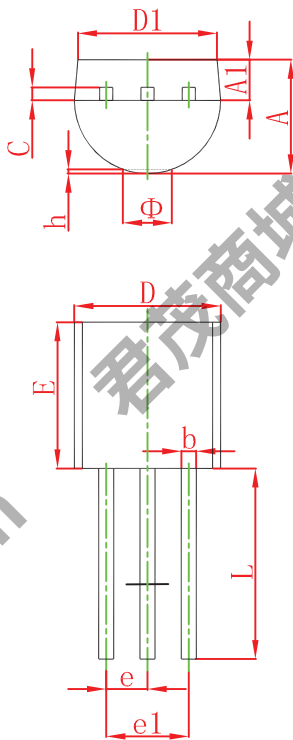
$R_{DS(ON)}$ — V_{GS}



I_S — V_{SD}

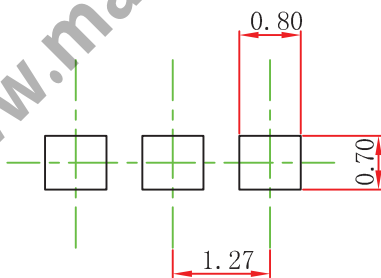


TO-92 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.300	4.700	0.169	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270 TYP		0.050 TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Φ		1.600		0.063
h	0.000	0.380	0.000	0.015

TO-92 Suggested Pad Layout



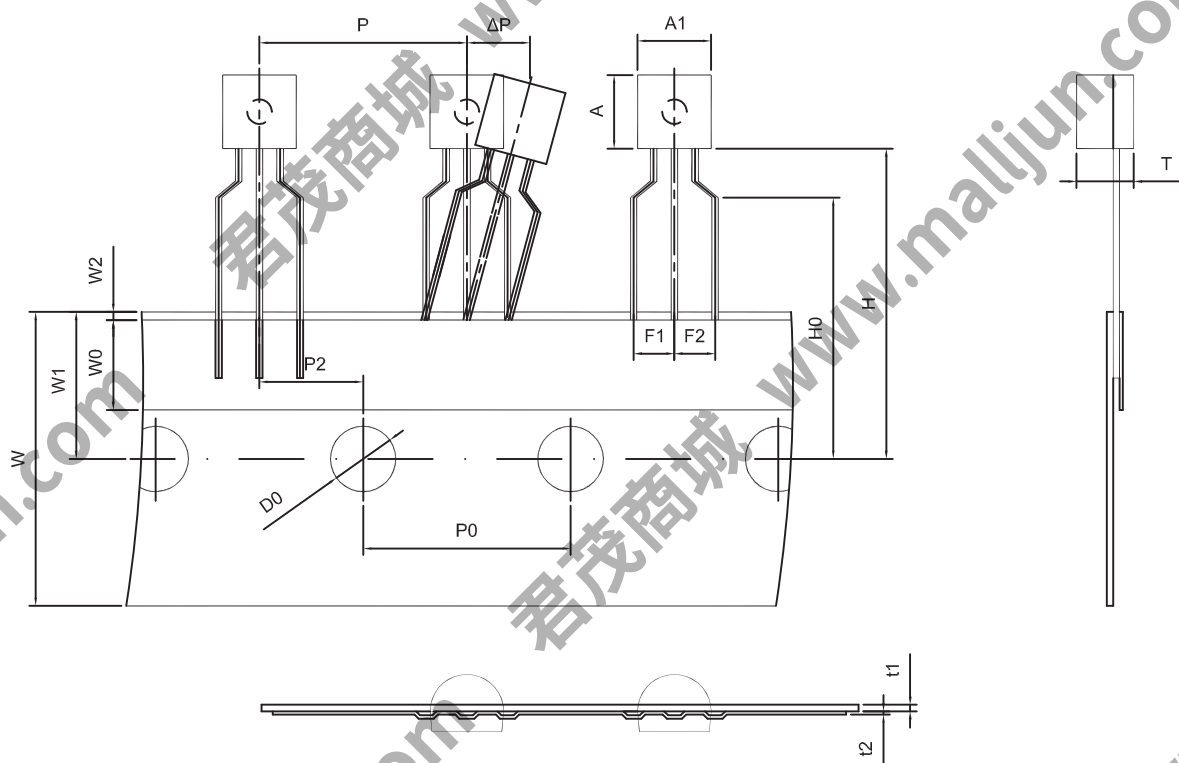
Note:

1. Controlling dimension: In millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

NOTICE

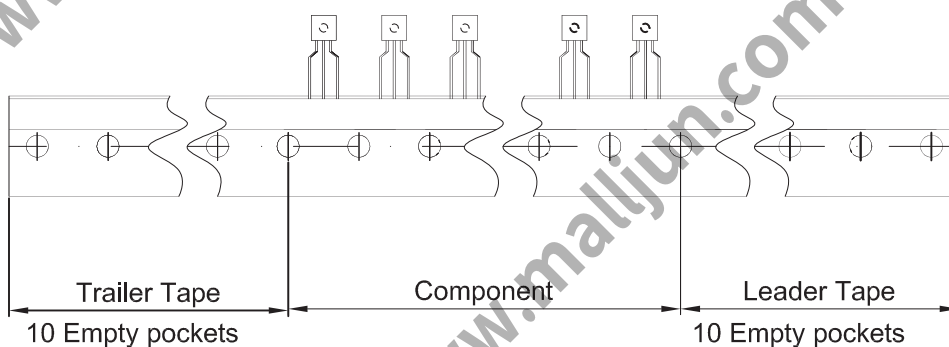
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TO-92 PACKAGE TAPEING DIMENSION



Dimiensions are in millimeter

A1	A	T	P	P0	P2	F1	F2	W
4.5	4.5	3.5	12.7	12.7	6.35	2.5	2.5	18.0
W0	W1	W2	H	H0	D0	t1	t2	ΔP
6.0	9.0	1.0 MAX.	19.0	16.0	4.0	0.4	0.2	0



Package	Box	Box Size(mm)	Carton	Carton Size(mm)
TO-92	2000 pcs	333×162×43	20,000 pcs	350×340×250